

(5) (((bl bitline bit adj line readline read adj line sense adj line c
 (0) ((bl buried adj (bl bitline bit adj line readline read adj line ser
 (1) ((bl buried adj (bl bitline bit adj line readline read adj line ser
 (2468604) connection strap
 (6425788) connect \$4 strap
 (41994) (bl bitline bit adj line readline read adj line sense adj line
 (2) (((bl bitline bit adj line readline read adj line sense adj line c
 (154) (((bl bitline bit adj line readline read adj line sense adj line
 (28) (((bl bitline bit adj line readline read adj line sense adj line
 (26) (((bl bitline bit adj line readline read adj line sense adj line
 (2) 6268243.pn.
 (562187) capacitor
 (62) (((bl buried adj (bl bitline bit adj line readline read adj line
 (9) ("4737828" | "4896293" | "5155059" | "5170243" | "52
 (4) 5840591.URPN
 (3) ("5618745" | "5827092" | "5829228".PN
 (4) 5840591.URPN
 (82) (((bl buried adj (bl bitline bit adj line readline read adj line
 (26) (((bl bitline bit adj line readline read adj line sense adj line
 (74) 5840591.URPN : (((bl buried adj (bl bitline bit adj line read

Buttons: Browse Queue Clear

DOCs: USPAT, US-PGPUB, EPO, JPO, DERWENT, IBM, YDB

Default operator: OR

5840591.URPN: (((bl buried adj (bl bitline bit adj line readline read adj line sense adj line : column)
) and (((bl bitline bit adj line readline read adj line sense adj line : column)
) near9 trench) same ((bl bitline bit adj line readline read adj line sense adj line : column)
) near9 (etch\$4 trim\$4))) no1 micron.as.) and capacitor) (((bl bitline bit adj line readline read adj line sense adj line : column)
) near9 trench) same ((bl bitline bit adj line readline read adj line sense adj line : column)
) near9 (etch\$4 trim\$4)) same ((bl bitline bit adj line readline read adj line sense adj line : column)
) near (connect\$4 strap))) and ((bl bitline bit adj line readline read adj line sense adj line : column)
)

March 2004

#	Operator	Document#	Issue#	Title	Current	CurrentXB	Reviewal	S	C	P	Image	Doc#	P
1	Park, Jae-Kw	US 5840591	1998:1	Method of manufacturing buried bit line DRA	438/262:257/E21.64							US 5840591	
2	Lee, Robin et	US 6303424	2001:1	Method for fabricating a buried bit line in a D	438/238:257/E21.65							US 6303424	
3	Chen, Min-Lia	US 6271558	2001:0	High density memory structure	257/303:257/301							US 6271558	
4	Lee, Tong-Hsi	US 6127228	2000:1	Method of forming buried bit line	438/262:257/E21.50							US 6127228	
5	Lee, Kang-ye	US 5900659	1999:0	Buried bit line DRAM cells	257/296:257/306							US 5900659	
6	Divakaruni, R	US 2003011	2003:0	DRAM array bit contact with relaxed pitch p	257/200							US 2003011	
7	Beer, Peter	US 2003001	2003:0	Integrated semiconductor memory and fabric	257/296							US 2003001	
8	Divakaruni, R	US 2003000	2003:0	Modified vertical MOSFET and methods of fo	257/330:257/332							US 2003000	
9	Asano, Isamu	US 2002015	2002:0	Method of manufacturing a semiconductor in	438/253:257/E21.64							US 2002015	
10	HIEDA, KATS	US 2002015	2002:2	SEMICONDUCTOR DEVICE AND METHOD FO	257/306:257/E21.00							US 2002015	